

### MPSA05/FTSOA05 MPSA06/FTSOA06

NPN Small Signal General **Purpose Amplifiers** 

VCEO ... 60 V (Min) (MPS/FTSOA05), 80 V (Min) (MPS/FTSOA06)

h<sub>FE</sub> ... 50 (Min) @ 10 mA and 100 mA

V<sub>CE(sat)</sub> ... 0.25 V (Max) @ 100 mA

Complements ... MPS/FTSOA55, MPS/FTSOA56, (PNP)

**PACKAGE** 

MPSA05 MPSA06

FTSOA05 FTSOA06

TO-92 TO-236AA/AB TO-236AA/AB

TO-92

### ABSOLUTE MAXIMUM RATINGS (Note 1)

Temperatures

-55° C to 150° C Storage Temperature 150°C Operating Junction Temperature

Power Dissipation (Notes 2 & 3)

MPS **FTSO** Total Dissipation at 0.350 W\* 0.625 W 25° C Ambient Temperature 0.400 W 70° C Ambient Temperature 1.0 W 25°C Case Temperature

A05 A06 Voltages & Currents V<sub>CEO</sub> Collector to Emitter Voltage 60 V 80 V (Note 4) 80 V 60 V V<sub>CBO</sub> Collector to Base Voltage 4.0 V Emitter to Base Voltage 4.0 V VEBO 500 mA 500 mA Collector Current

# ELECTRICAL CHARACTERISTICS (25°C Ambient Temperature unless otherwise noted) (Note 6)

		Α	05	A	06		
SYMBOL	CHARACTERISTIC	MIN	MAX	MIN	MAX	UNITS	TEST CONDITIONS
BV <sub>CEO</sub>	Collector to Emitter Breakdown Voltage	60		80		V	I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0
ВУЕВО	Emitter to Base Breakdown Voltage	4.0		4.0		V	$I_E = 100 \ \mu A, I_C = 0$
Ісво	Collector Cutoff Current		100		100	nA nA	$\begin{vmatrix} V_{CB} = 60 \text{ V}, I_{E} = 0 \\ V_{CB} = 80 \text{ V}, I_{E} = 0 \end{vmatrix}$

#### NOTES:

- These ratings are limiting values above which the serviceability of any individual semiconductor device may be impaired.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

  These ratings give a maximum junction temperature of 150°C and (TO-92) junction-to-case thermal resistance of 125°C/W (derating factor of 8.0 mW/°C); junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance of 200°C/W (derating factor of 5.0 mW/°C); (TO-236) junction-to-ambient thermal resistance o
- mw/-C); function-to-attracting trends resistance of 255 C/M (derating factor of 2.8 mW° C).
  Rating refers to a high current point where collector to emitter voltage is lowest.
- Pulse conditions: length = 300 µs; duty cycle = 1%.
  For product family characteristic curves, refer to Curve Set T149.
- Package mounted on 99.5% alumina 8 mm x 8 mm x 0.6 mm.

## MPSA05/FTSOA05 7-29-23 MPSA06/FTSOA06

# ELECTRICAL CHARACTERISTICS (25° C Ambient Temperature unless otherwise noted) (Note 6)

SYMBOL	CHARACTERISTIC	A05		A06			
		MIN	MAX	MIN	MAX	UNITS	TEST CONDITIONS
h <sub>FE</sub>	DC Current Gain (Note 5)	50 50		50 50			$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage (Note 5)		0.25		0.25	V	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$
V <sub>BE(ON)</sub>	Base to Emitter "On" Voltage		1.2		1.2	l v	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1.0 V
fτ	Current Gain Bandwidth Product	50		50		MHz	I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 1.0 V, f = 100 MHz

